

Spin scattering in nonmagnetic semiconductors

Spin state

Wave function: $|\psi(\mathbf{k}, s)\rangle = \varphi_{\uparrow}|\mathbf{k}, \uparrow\rangle + \varphi_{\downarrow}|\mathbf{k}, \downarrow\rangle$

Spin density matrix: $\rho = |\psi(\mathbf{k}, s)\rangle\langle\psi(\mathbf{k}, s)| = \begin{pmatrix} \rho_{\uparrow\uparrow} & \rho_{\uparrow\downarrow} \\ \rho_{\downarrow\uparrow} & \rho_{\downarrow\downarrow} \end{pmatrix}$

In general, it should be

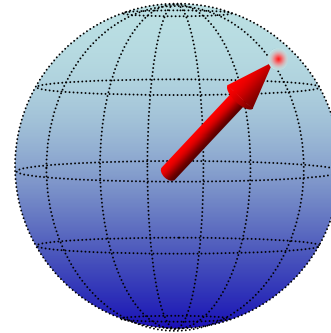
$$\rho(\mathbf{k}, \mathbf{k}'; s, s')$$

Use Wigner's function to get

$$\rho(\mathbf{K}, \mathbf{R}; s, s')$$

OR

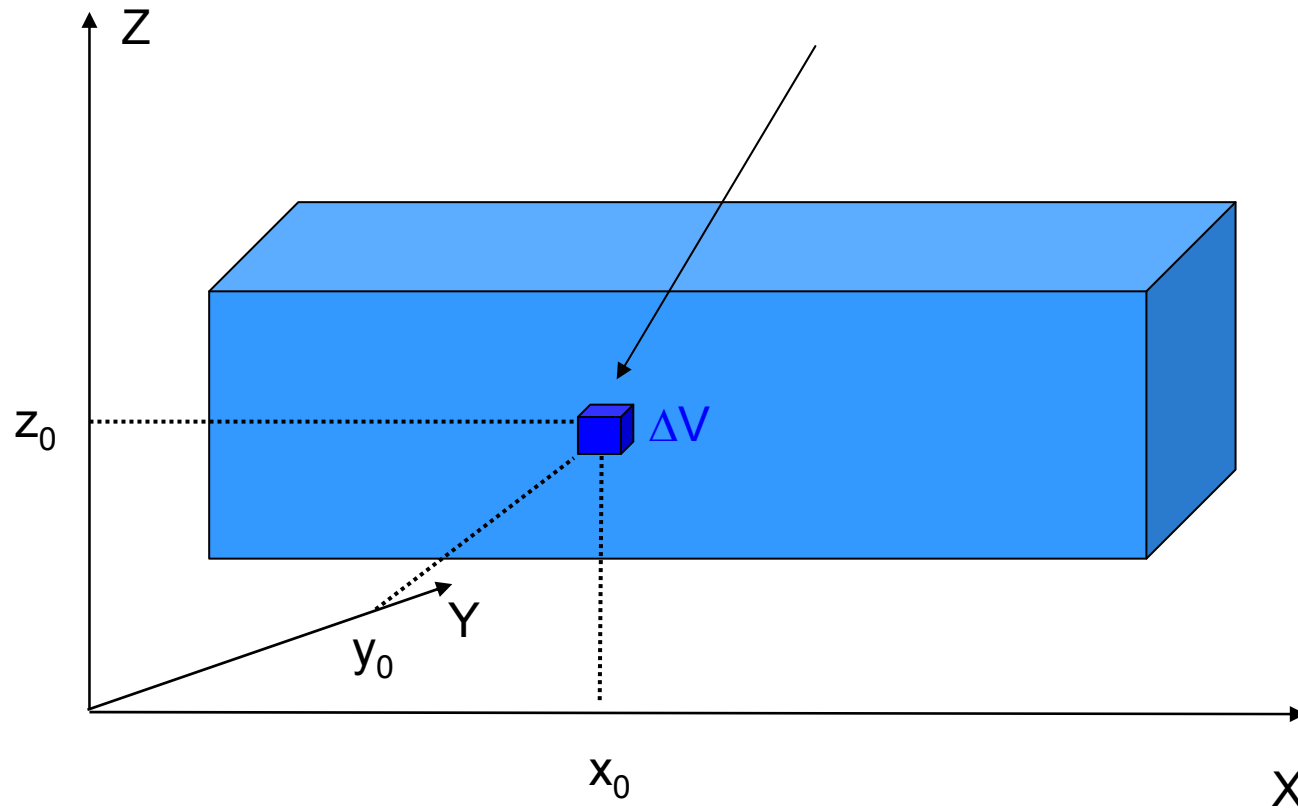
Spin polarization vector: $\vec{P} = (P_x, P_y, P_z)$



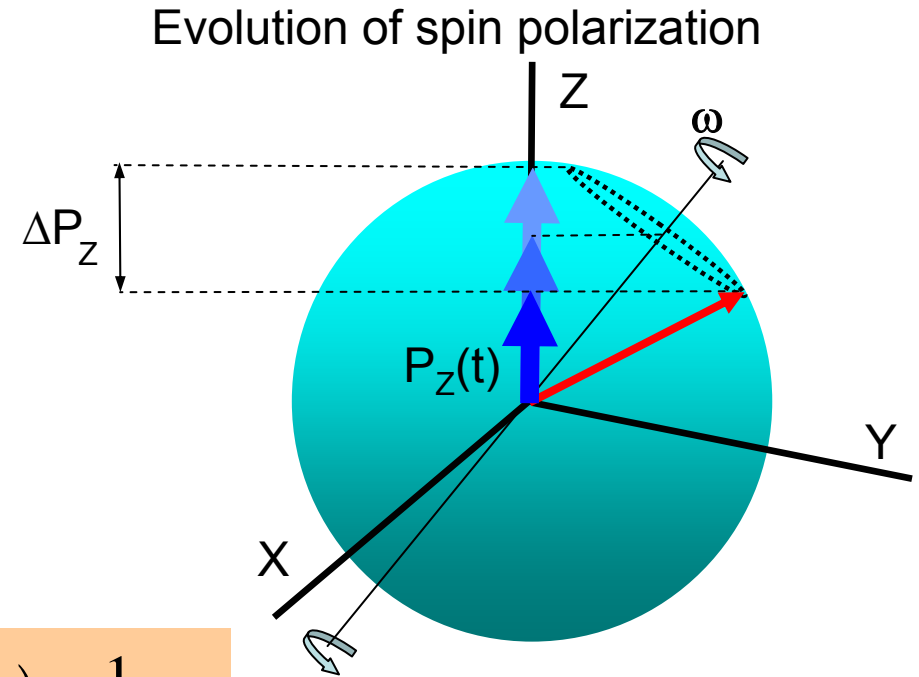
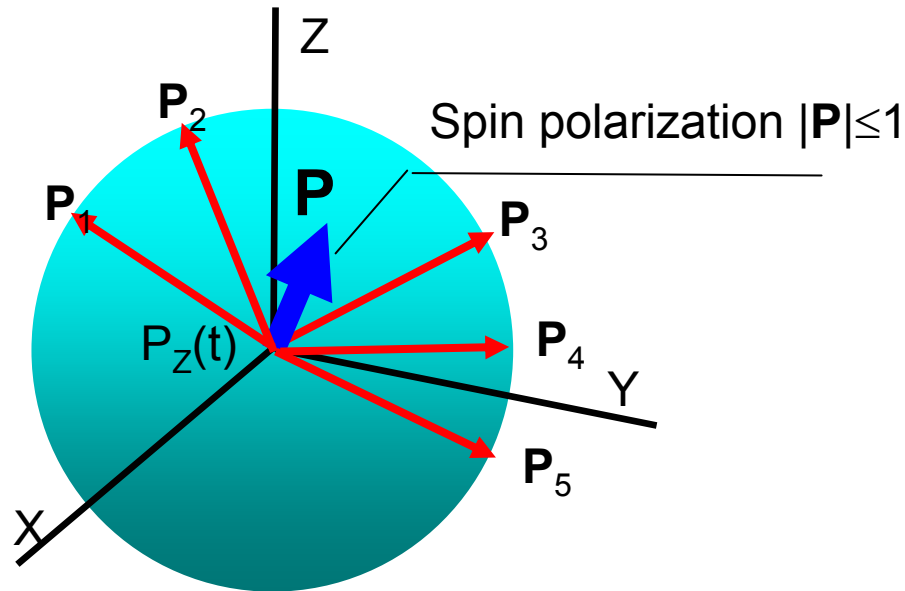
$$\rho_s = \frac{1}{2} \begin{pmatrix} 1 + P_z & P_x - iP_y \\ P_x + iP_y & 1 - P_z \end{pmatrix}$$

Local spin polarization

Number of electrons: $N=n \cdot \Delta V$
Magnetic moment: $\mathbf{M}=N \cdot \mu_B \cdot \mathbf{P}$



Spin polarization vector



Bloch equation:

$$\frac{d\vec{P}}{dt} = \gamma \vec{P} \times \vec{B} - \frac{1}{T_1} (\vec{P}_{\parallel} - \vec{P}_0) - \frac{1}{T_2} \vec{P}_{\perp}$$

Spin scattering is here

Today we talk about T_1 processes

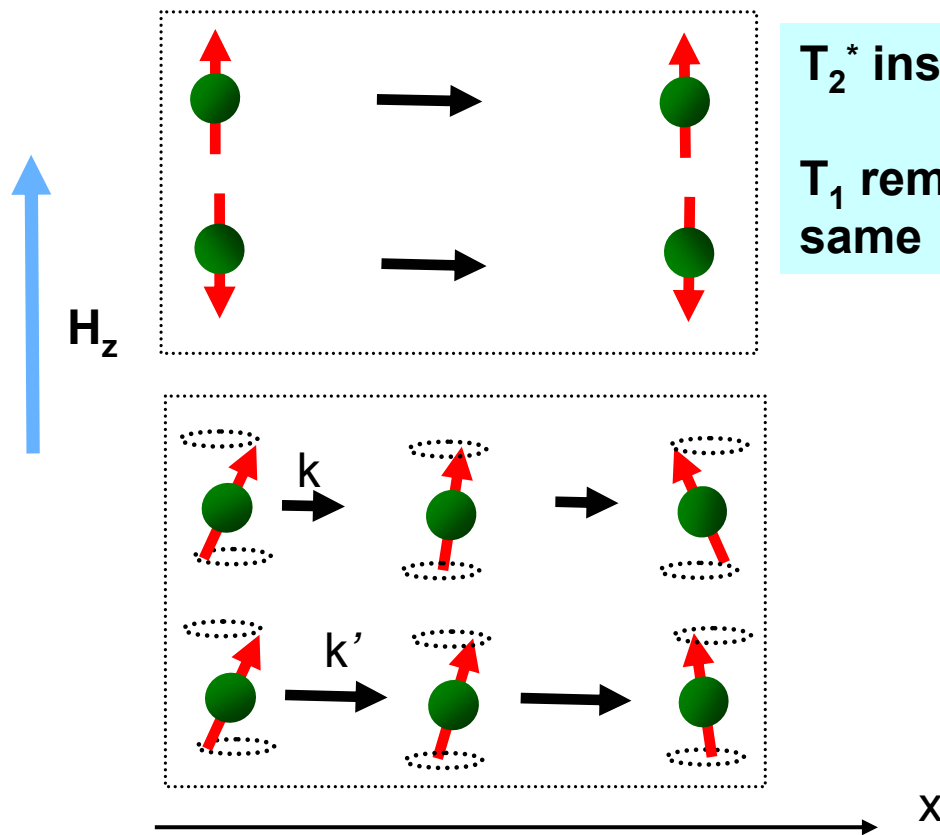
Evolution of spin polarization vector

Interaction with magnetic field

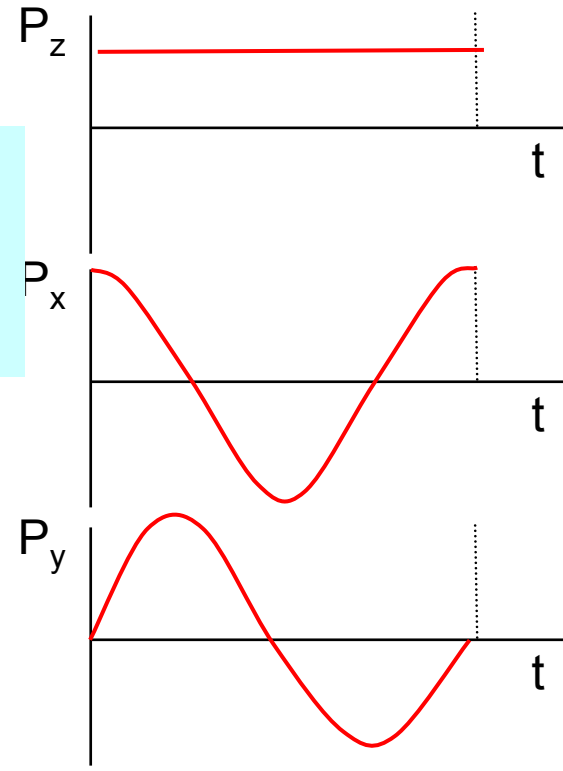
$$H = -\boldsymbol{\mu}\mathbf{H} = g\mu_B\mathbf{S}\mathbf{H}$$

$$\mu_B = 9.27 \times 10^{-24} \text{ J/T}$$

No scattering!
Pure dephasing.



T_2^* instead of T_2
 T_1 remains the same



Spin scattering

T₁ processes

We have to define basis for spin \uparrow and \downarrow .
Use small magnetic field.

Spin-orbit interaction

Elliot-Yafet mechanism

D'yakonov-Perel mechanism

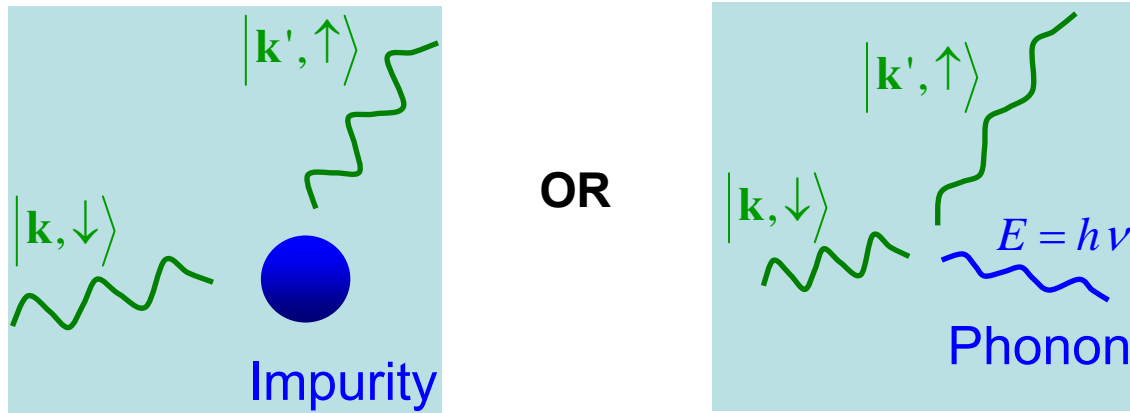
Hyperfine interaction with nuclear spins

Exchange with holes (Bir-Aronov-Pikus)

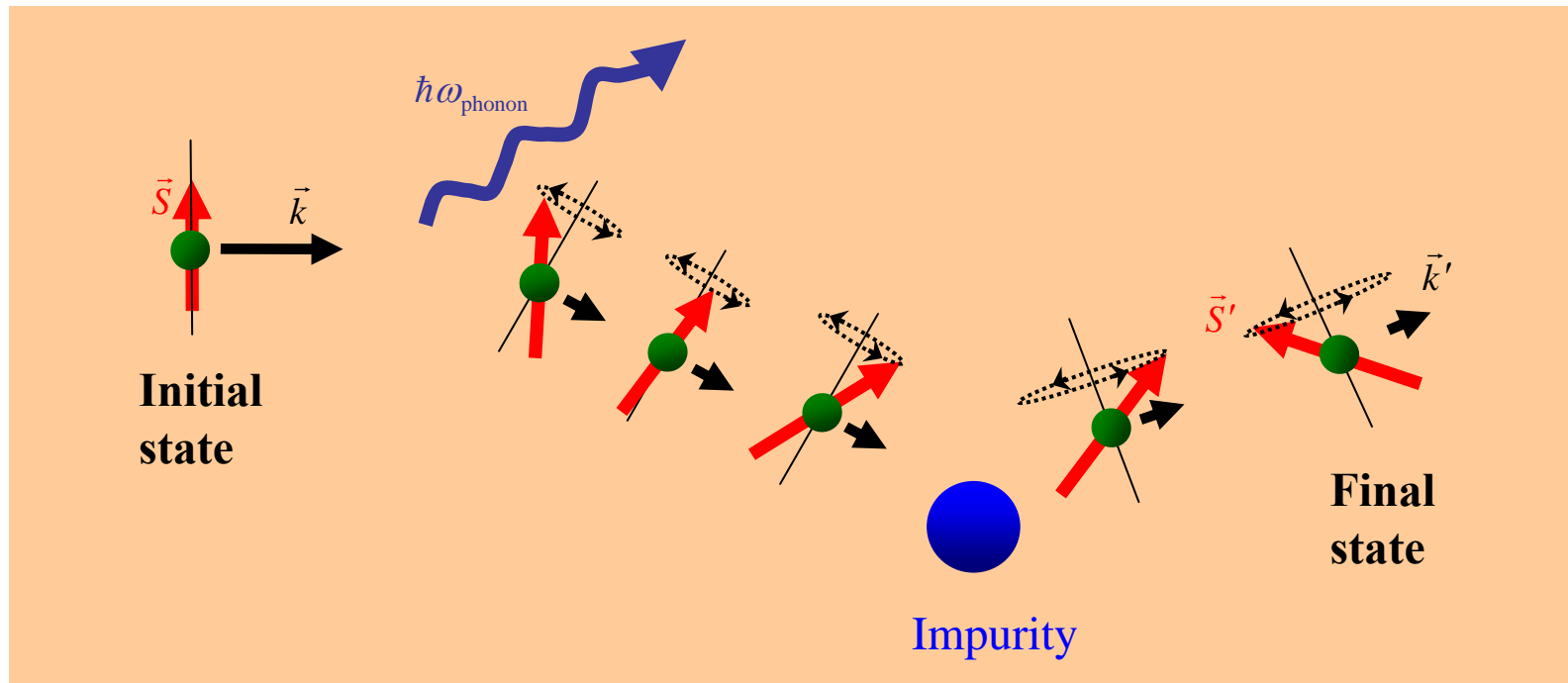
No direct interaction with phonons & non-magnetic impurities.

Spin flip vs. spin precession

Type I



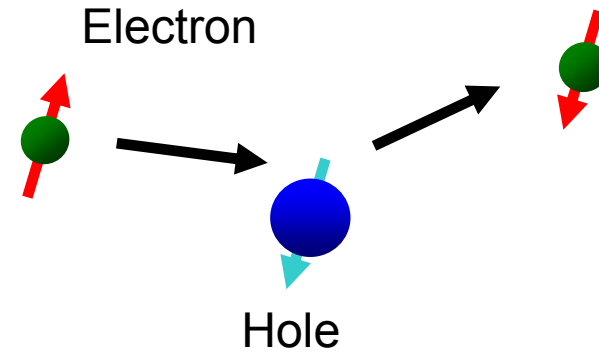
Type II



Electron-hole exchange

Important in p-type semiconductors

Exchange Hamiltonian: $H_{exch} = A\mathbf{J}\mathbf{S}\delta(\mathbf{r})$

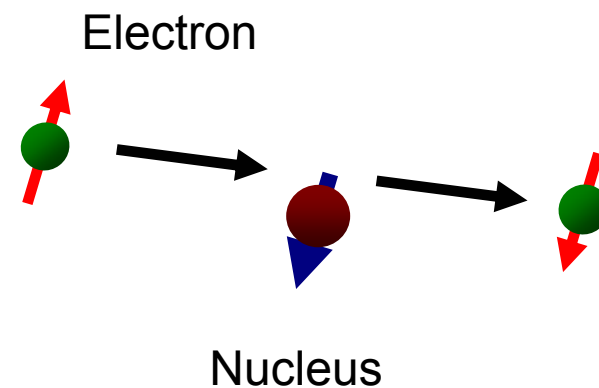


momentum and J can relax

Hyperfine interaction

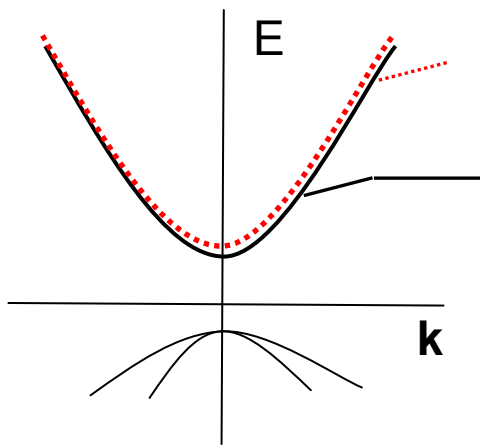
Hyperfine Hamiltonian: $H_{Hf}(\mathbf{r}) = A\mathbf{S}\mathbf{I}\delta(\mathbf{r})$

Suppressed in strong magnetic fields



Elliott-Yafet mechanism

Spin states: $|\mathbf{k}, \downarrow\rangle$ $|\mathbf{k}, \uparrow\rangle$

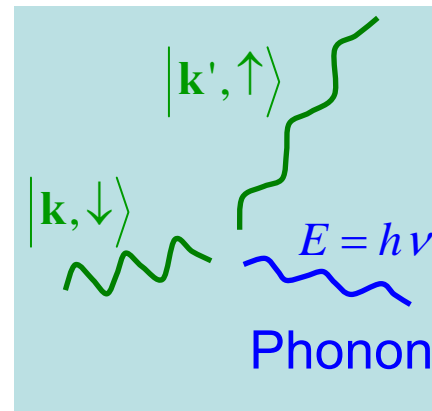
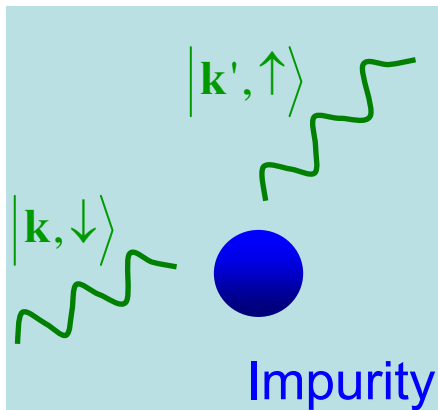


mixes pure spin up and down states

$$|k, " \uparrow " \rangle = L^{-3/2} e^{i\mathbf{k}\mathbf{r}} \left(u_{\mathbf{k}}(\mathbf{r}) |\uparrow\rangle + v_{\mathbf{k}}(\mathbf{r}) |\downarrow\rangle \right)$$

$$|k, " \downarrow " \rangle = L^{-3/2} e^{i\mathbf{k}\mathbf{r}} \left(u'_{\mathbf{k}}(\mathbf{r}) |\downarrow\rangle + v'_{\mathbf{k}}(\mathbf{r}) |\uparrow\rangle \right)$$

Any momentum scattering can result in a spin flip.

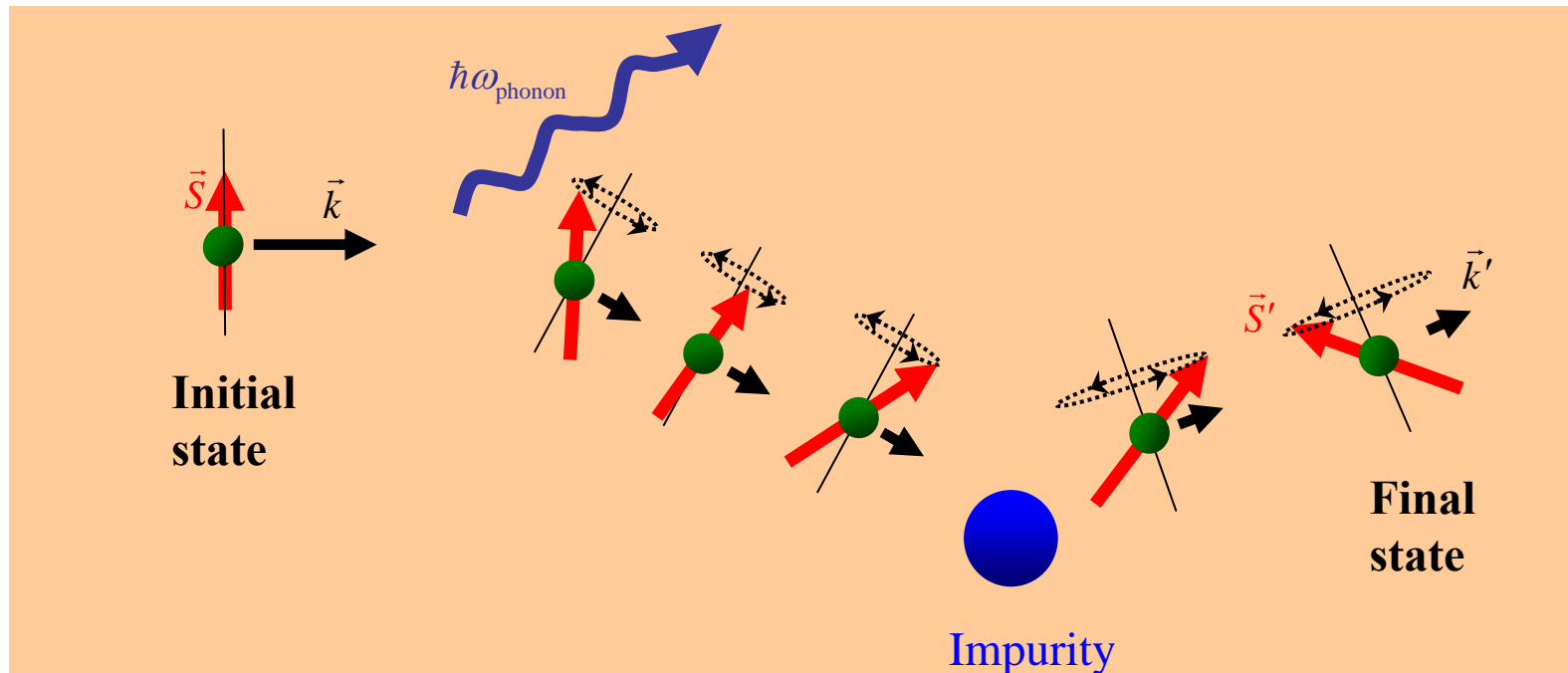
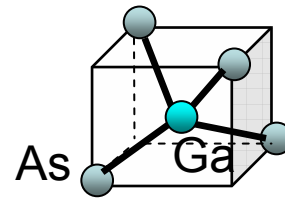


D'yakonov-Perel' mechanism

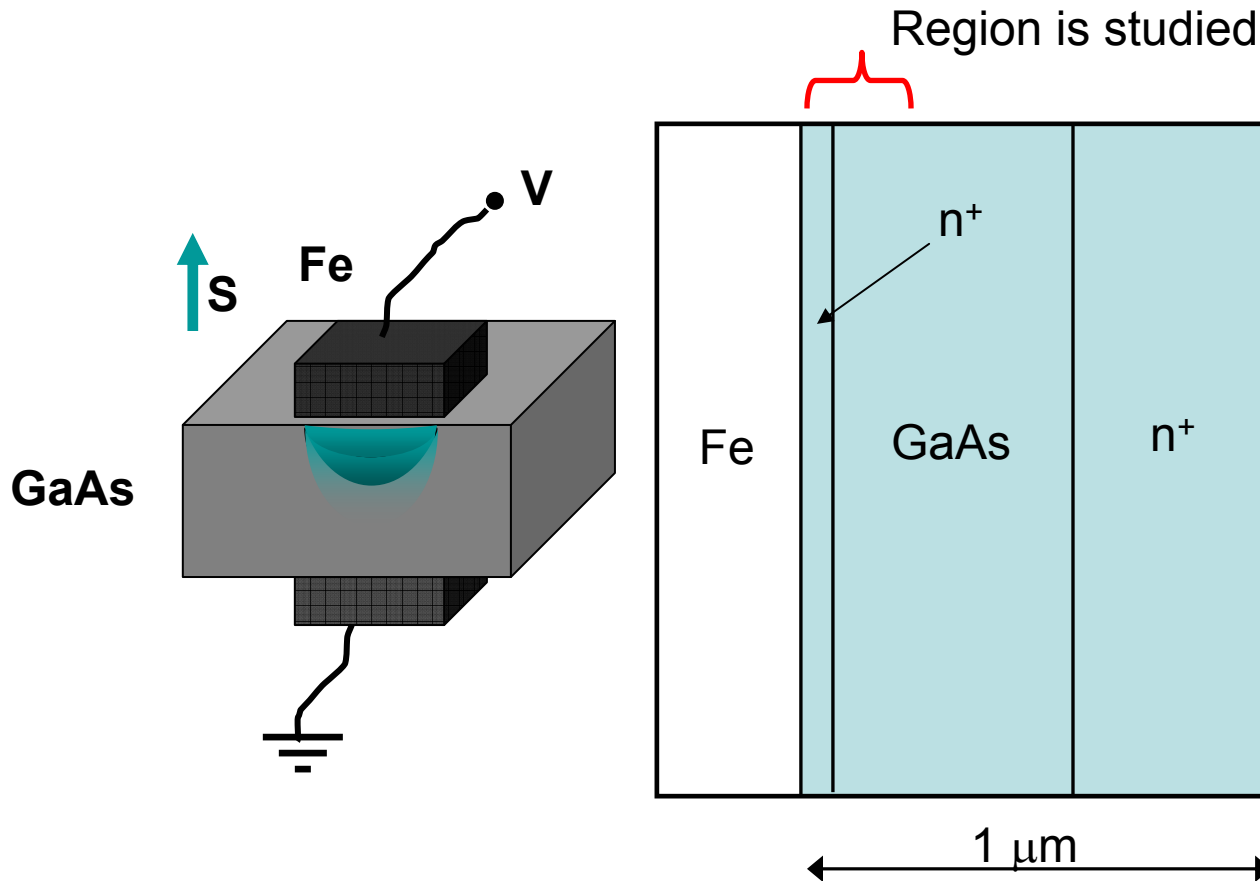
Spin-orbit interaction:

$$H_{SO} = \alpha_{\Gamma} \left\{ \sigma_x k_x (k_y^2 - k_z^2) + \sigma_y k_y (k_z^2 - k_x^2) + \sigma_z k_z (k_x^2 - k_y^2) \right\}$$

Crystals without a center of inversion



D-P scattering in a device structure, example



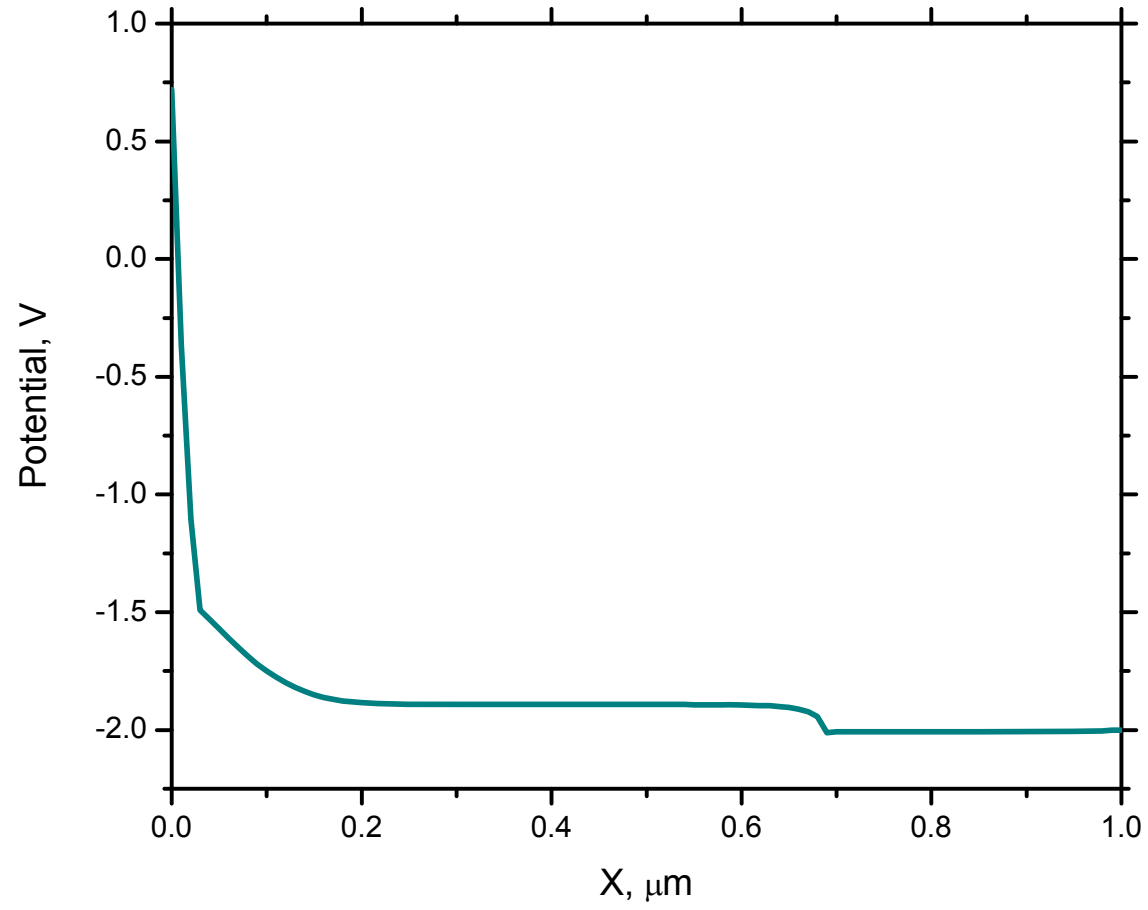
$$q\phi_B = 0.72 \text{ eV}$$

$$\alpha_\Gamma = 28 \text{ eVA}^3$$

$$\alpha_L = 0.27 \text{ eVA}$$

$$\alpha_X = 0.087 \text{ eVA}$$

Potential Profile, $V_{ds} = 2\text{ V}$



Model for Monte-Carlo simulation

- Charge transport (BTE):

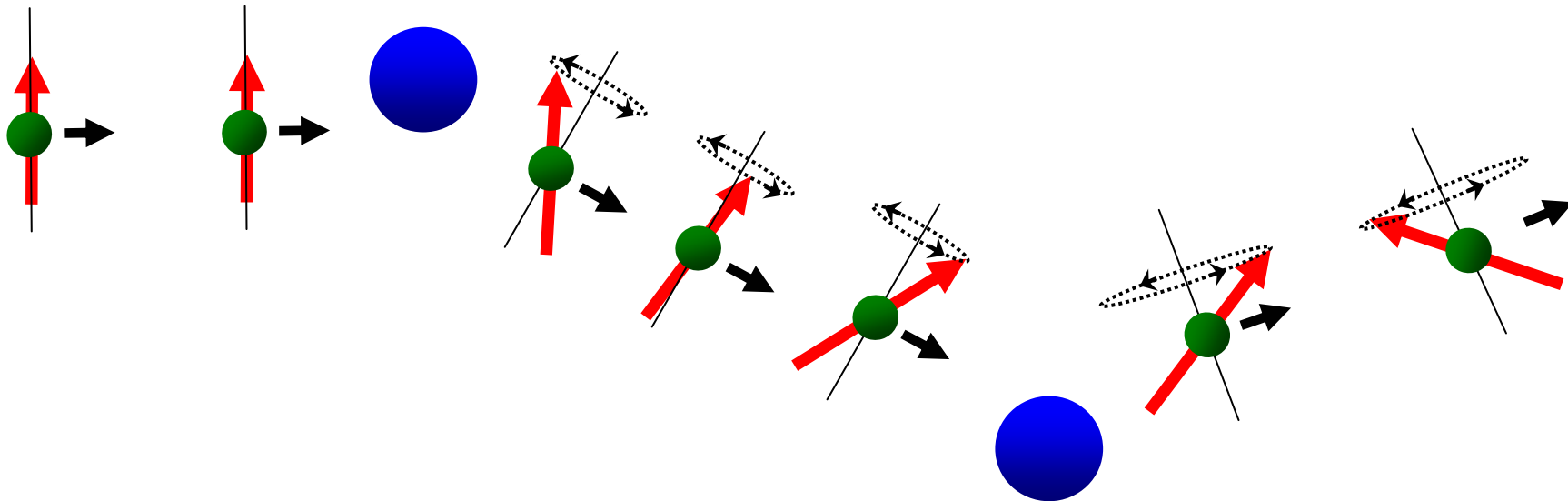
$$\frac{\partial f}{\partial t} + \mathbf{v} \cdot \nabla f - \frac{q}{\hbar} (\nabla V) \cdot \nabla_{\mathbf{k}} f = \left(\frac{\partial f}{\partial t} \right)_C$$

$$\nabla^2 V = -\frac{e^2}{\epsilon_s} (n(\mathbf{r}) - N_d)$$

- Spin density matrix evolution:

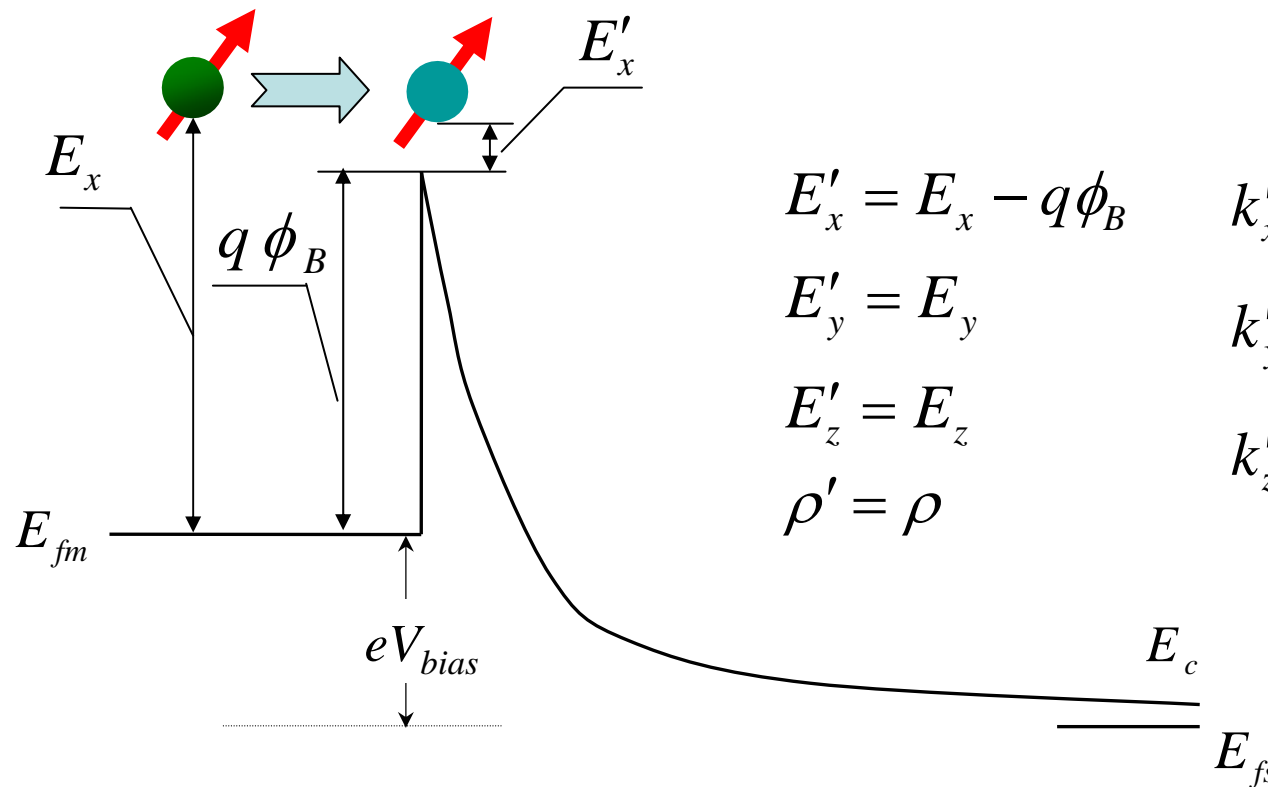
$$\rho_i(t + dt) = e^{-iH_{\text{so}}dt/\hbar} \rho_i(t) e^{iH_{\text{so}}dt/\hbar}$$

- Spin scattering mechanism:



Injection Mechanisms

- **Thermionic Emission:** $E_x > q\phi_B$ & spin is conserved



$$E'_x = E_x - q\phi_B$$

$$k'_x = \sqrt{2m^* E'_x} / \hbar$$

$$E'_y = E_y$$

$$k'_y = \pm \sqrt{2m^* E'_y} / \hbar$$

$$E'_z = E_z$$

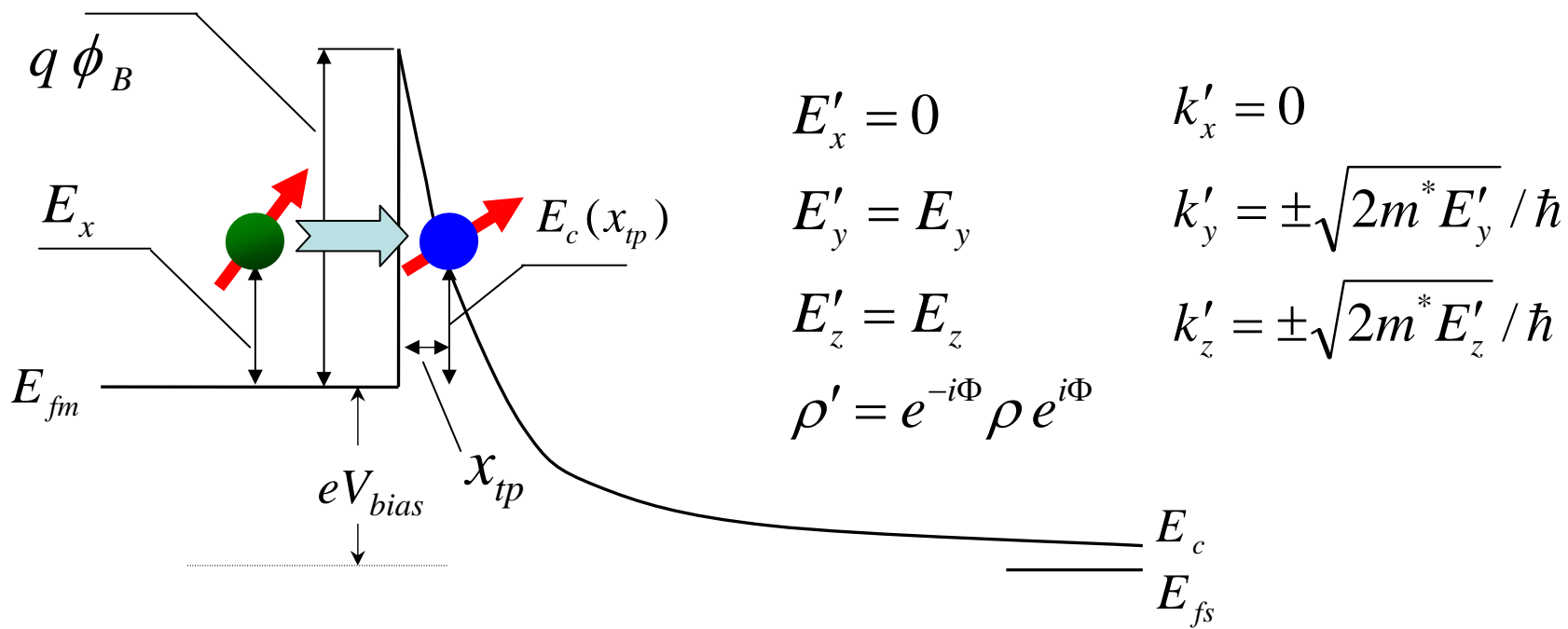
$$k'_z = \pm \sqrt{2m^* E'_z} / \hbar$$

$$\rho' = \rho$$

Injection Mechanisms

- **Tunneling through the Schottky barrier:** $E_x < q\phi_B$

Tunneling probability:
(WKB approximation)
$$T_{tp}(E) = \exp\left(-\frac{2}{\hbar} \int_0^{x_{tp}} \sqrt{2m^* [E_c(x) - E_x]} dx\right)$$



Electrons at the Ferromagnetic Contact

- Electron distribution function:

$$f(E) = \frac{1}{1 + e^{(E - E_{fm})/k_B T}} \sim e^{-(E - E_{fm})/k_B T}$$

- Equal average kinetic energy in x, y and z directions
- Probabilities of spin states are based on the densities of states

$$P_{\uparrow}(E) = \frac{D_{\uparrow}(E)}{D_{\uparrow}(E) + D_{\downarrow}(E)} \quad \text{and} \quad P_{\downarrow} = 1 - P_{\uparrow}$$

Spin-orbit couplings in 3 valleys of bulk GaAs

Dresselhaus Mechanism

1. Γ valley (000)

$$H_{SO} = \alpha_{\Gamma} \left\{ \sigma_x k_x (k_y^2 - k_z^2) + \sigma_y k_y (k_z^2 - k_x^2) + \sigma_z k_z (k_x^2 - k_y^2) \right\}$$

2. L valleys

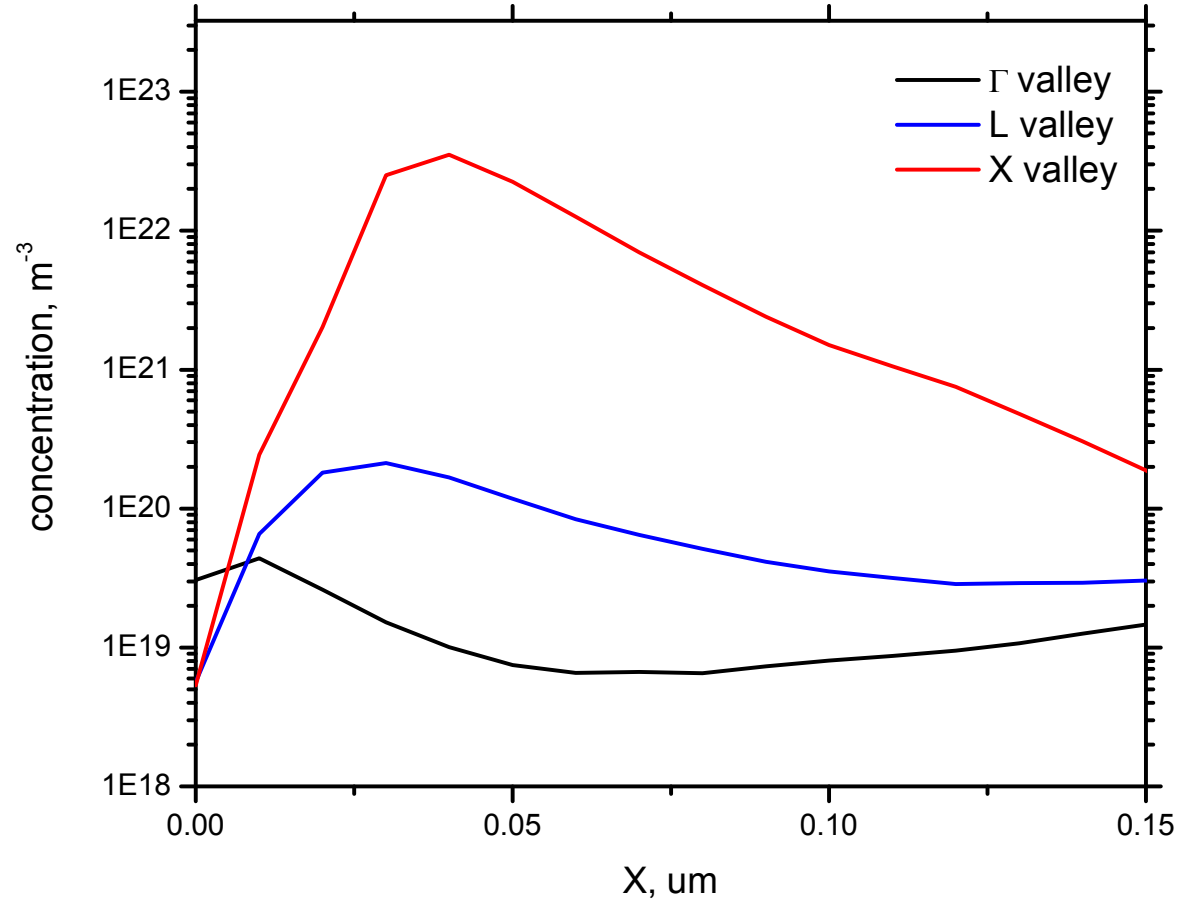
$$H_{SO} = \begin{cases} \alpha_L / \sqrt{3} \left\{ \sigma_x (k_y - k_z) + \sigma_y (k_z - k_x) + \sigma_z (k_x - k_y) \right\} & (1\ 1\ 1) \\ \alpha_L / \sqrt{3} \left\{ \sigma_x (k_y + k_z) - \sigma_y (k_x + k_z) + \sigma_z (k_y - k_x) \right\} & (-1\ -1\ 1) \\ \alpha_L / \sqrt{3} \left\{ \sigma_x (-k_y - k_z) + \sigma_y (k_x - k_z) + \sigma_z (k_x + k_y) \right\} & (-1\ 1\ -1) \\ \alpha_L / \sqrt{3} \left\{ \sigma_x (k_z - k_y) + \sigma_y (k_x + k_z) - \sigma_z (k_x + k_y) \right\} & (1\ -1\ -1) \end{cases}$$

3. X valleys

$$H_{SO} = \begin{cases} \alpha_X (\sigma_z k_z - \sigma_y k_y) & (\pm 1\ 1\ 1) \\ \alpha_X (\sigma_x k_x - \sigma_z k_z) & (1\ \pm 1\ 1) \\ \alpha_X (\sigma_x k_x - \sigma_y k_y) & (1\ 1\ \pm 1) \end{cases}$$

Carrier Concentration

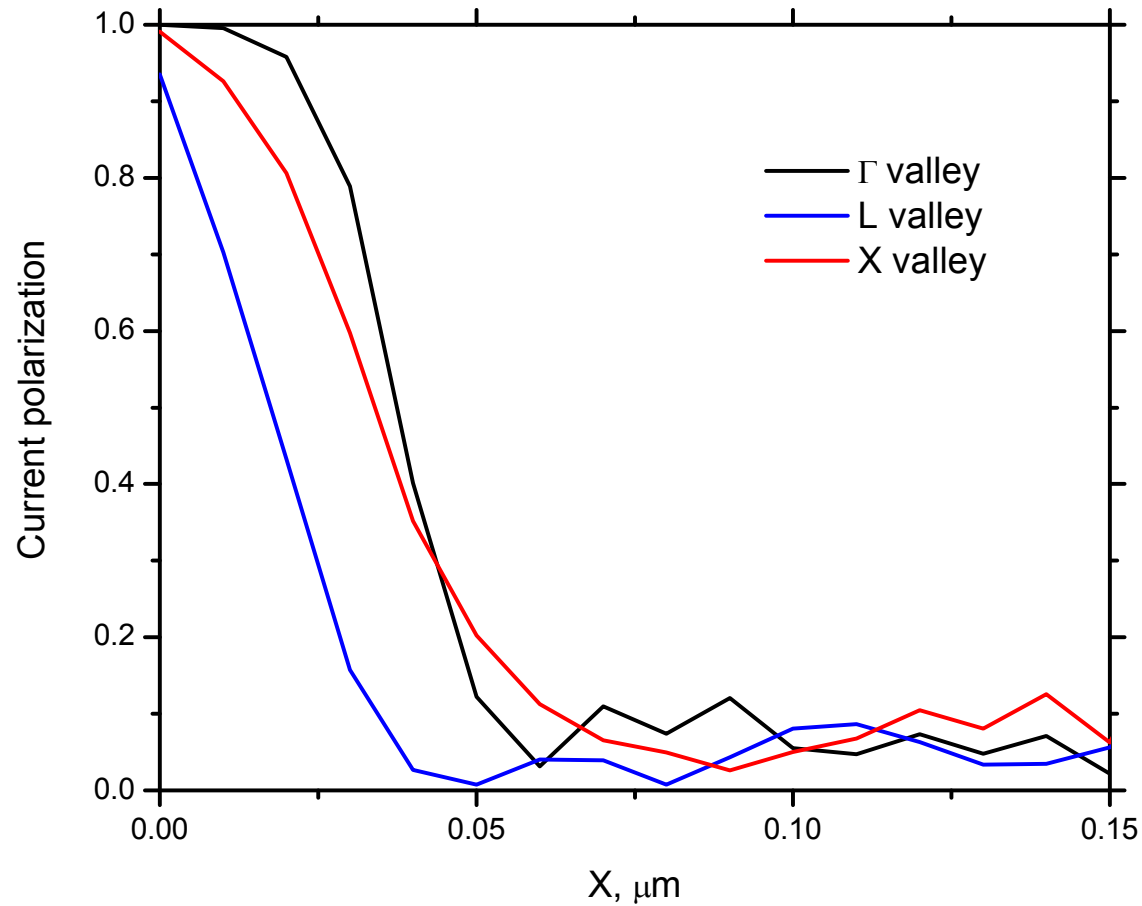
$T = 300 \text{ K}$, $V = 2 \text{ V}$



The extremely high electric field at the Schottky barrier pumps the electrons onto up valleys, especially the X valley

$T = 300 \text{ K}, V = 2 \text{ V}$

Current Spin Polarization

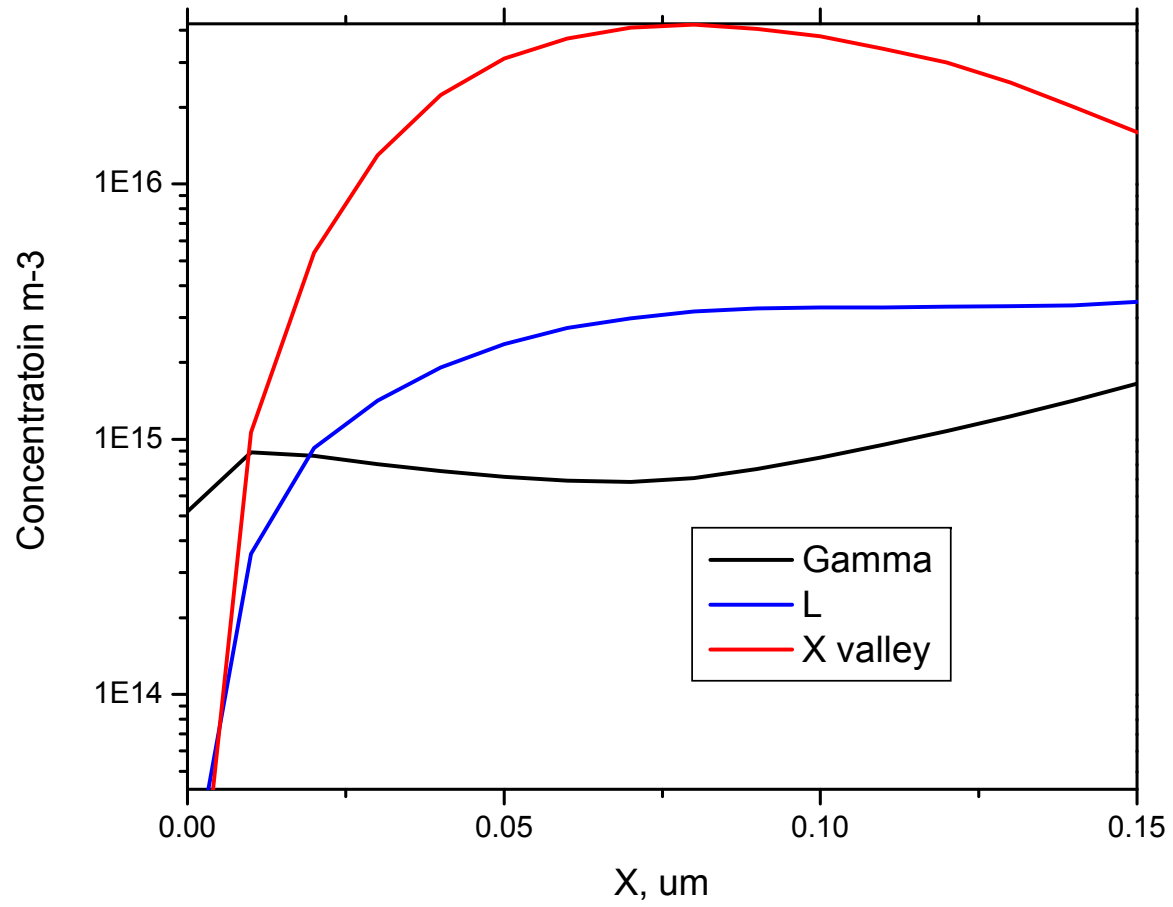


Spin dephasing is much stronger in upper valleys due stronger SO coupling

$T = 300 \text{ K}, V = 0.5 \text{ V}$

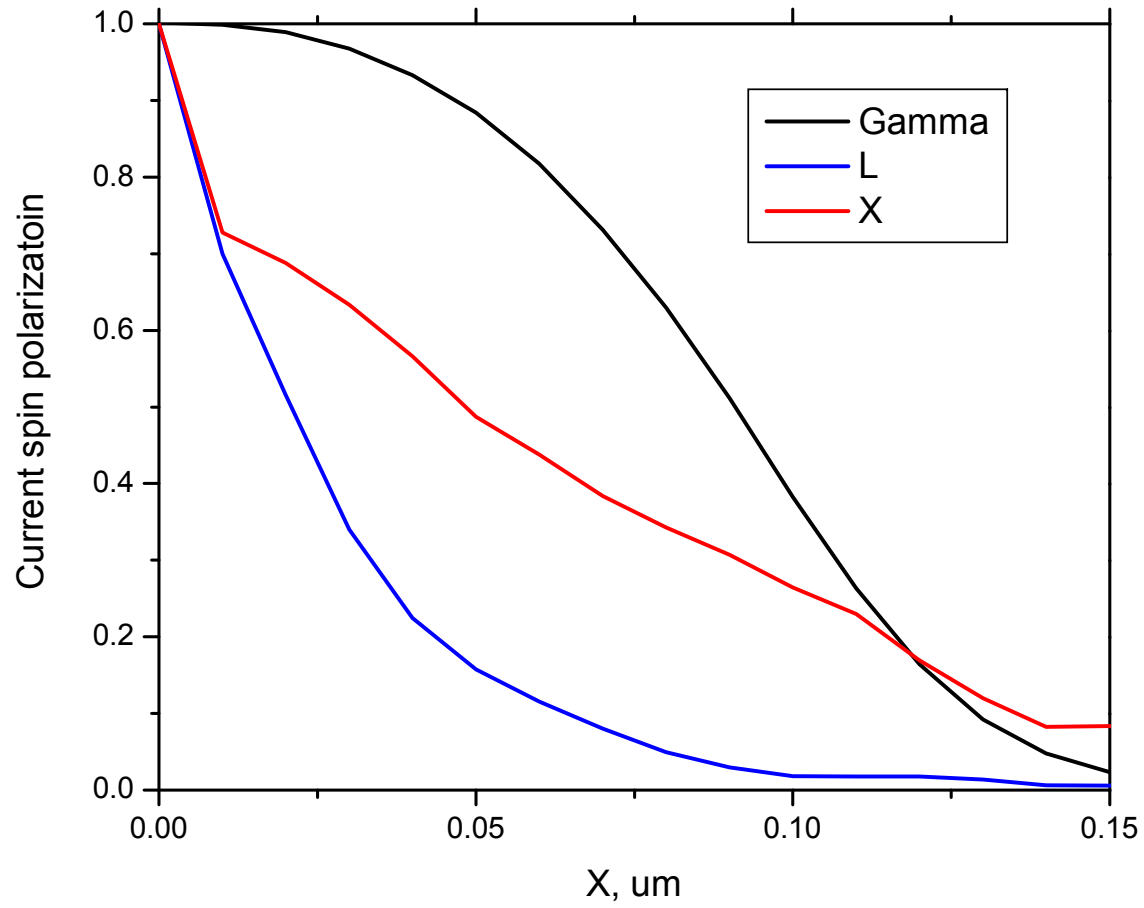
Low bias

Carrier Concentration



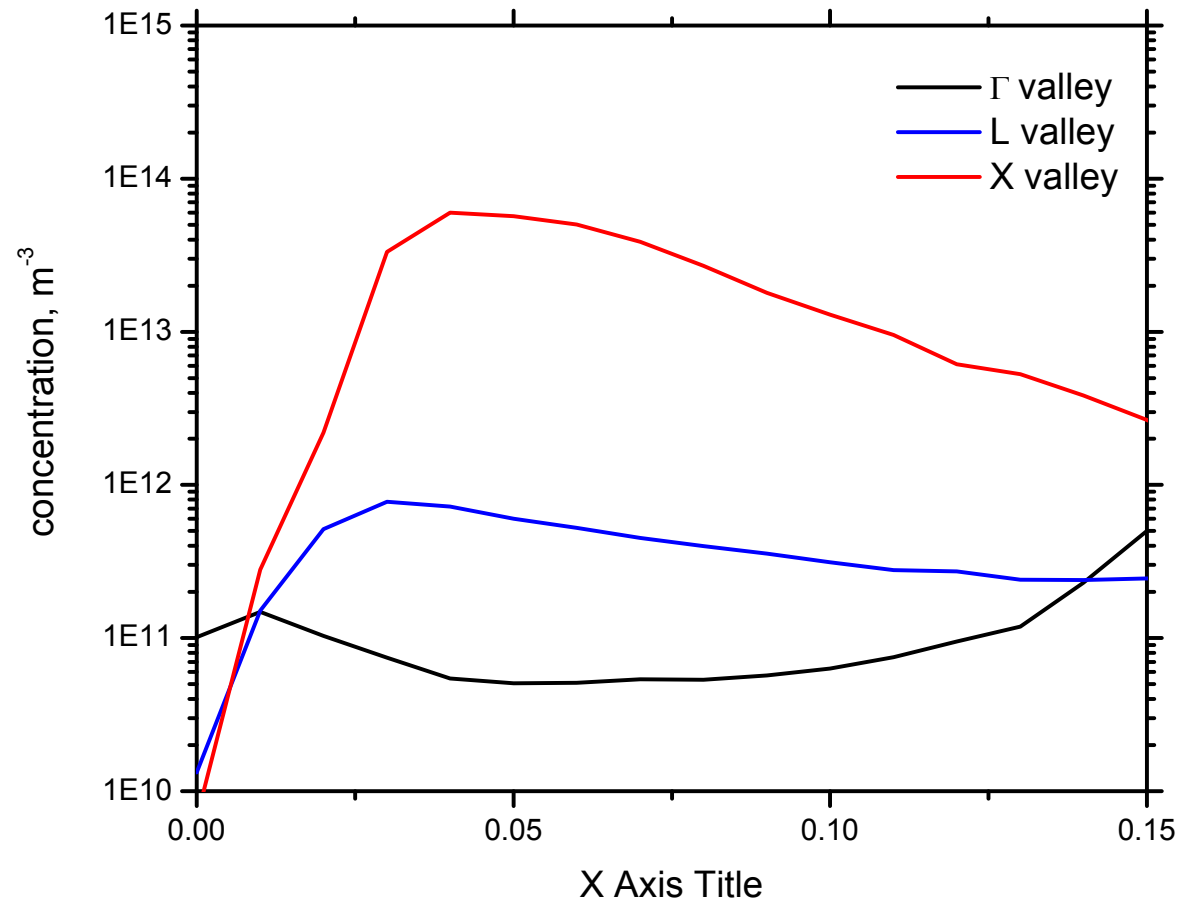
$T = 300 \text{ K}, V = 0.5 \text{ V}$

Current Spin Polarization



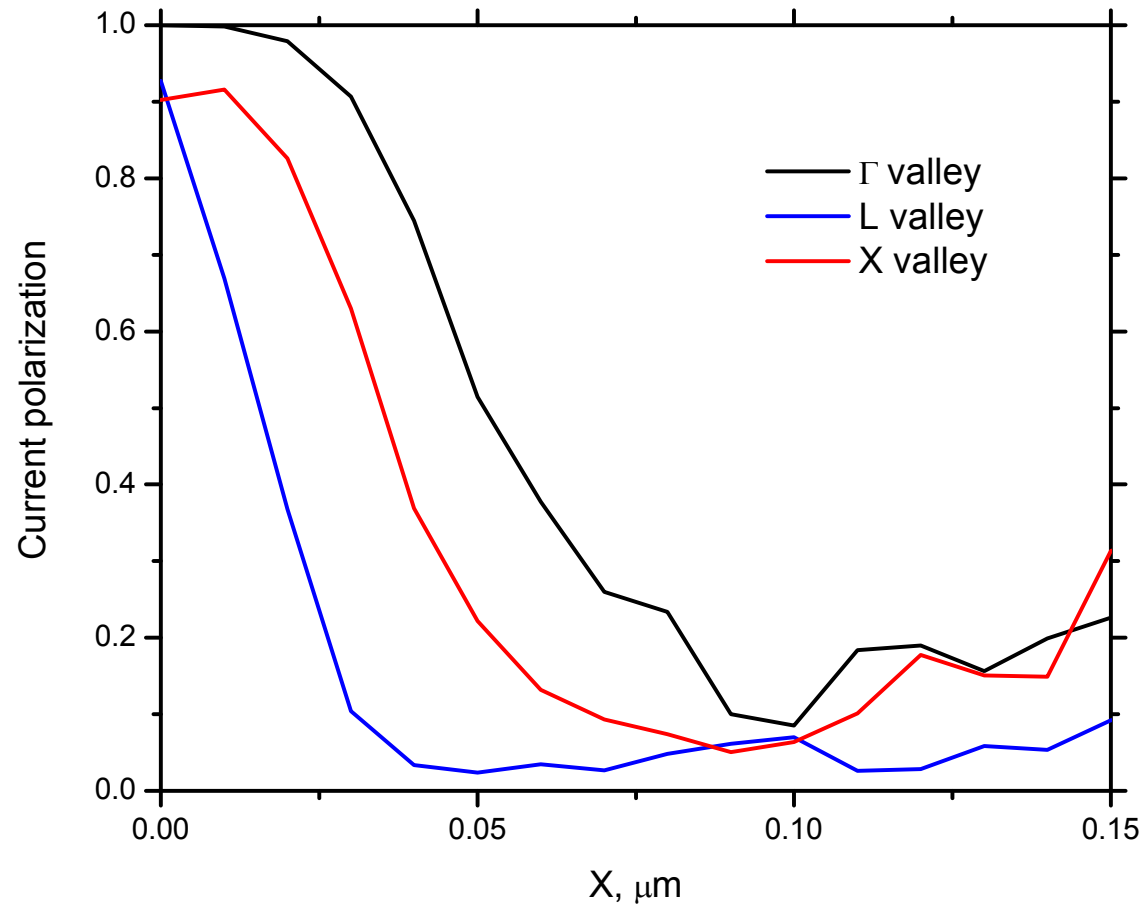
Low temperature $T = 80 \text{ K}$, $V = 2 \text{ V}$

Carrier Concentration

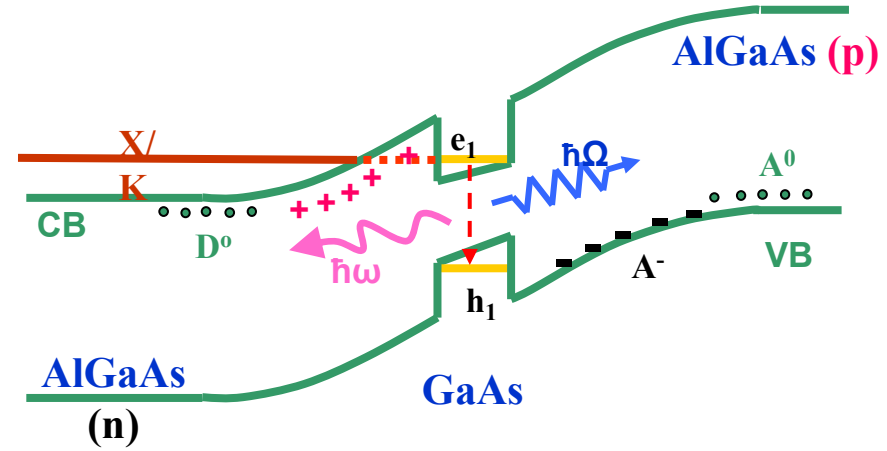
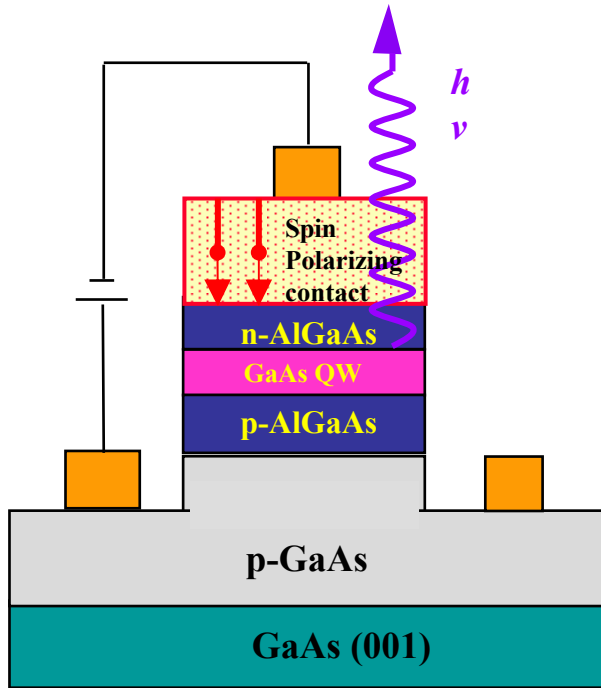


Low temperature $T = 80 \text{ K}$, $V = 2 \text{ V}$

Current Spin Polarization



Spin-LED

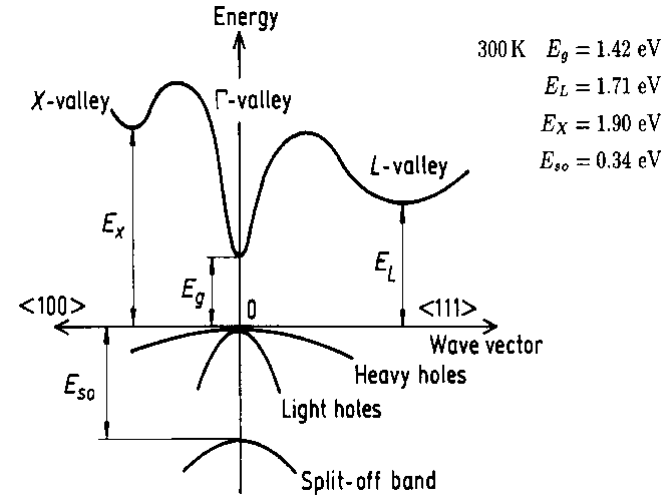
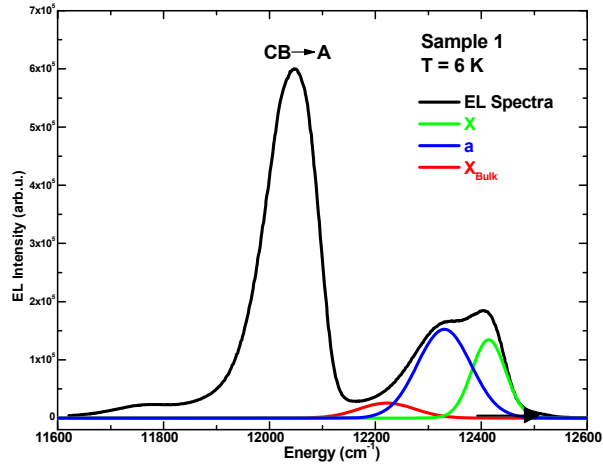


M. Yasar, PhD Thesis

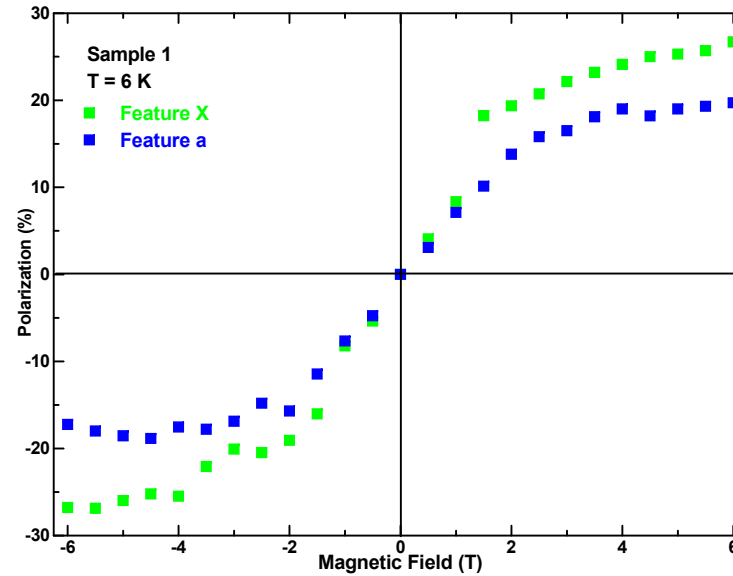
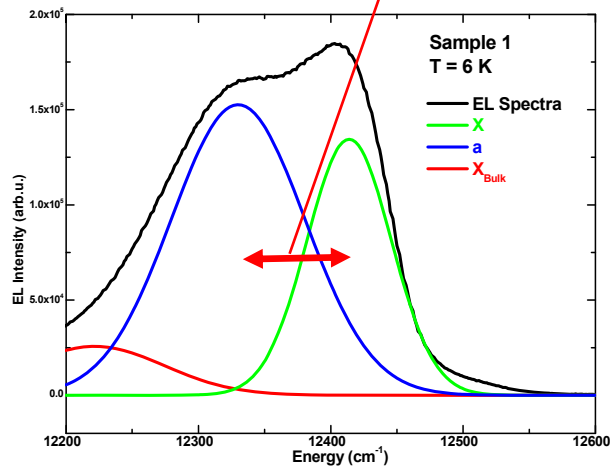
Spin-LED

R. Mallory, et. al., Phys. Rev. B 73, 115308 (2006)

Electroluminescence (1,0,0)

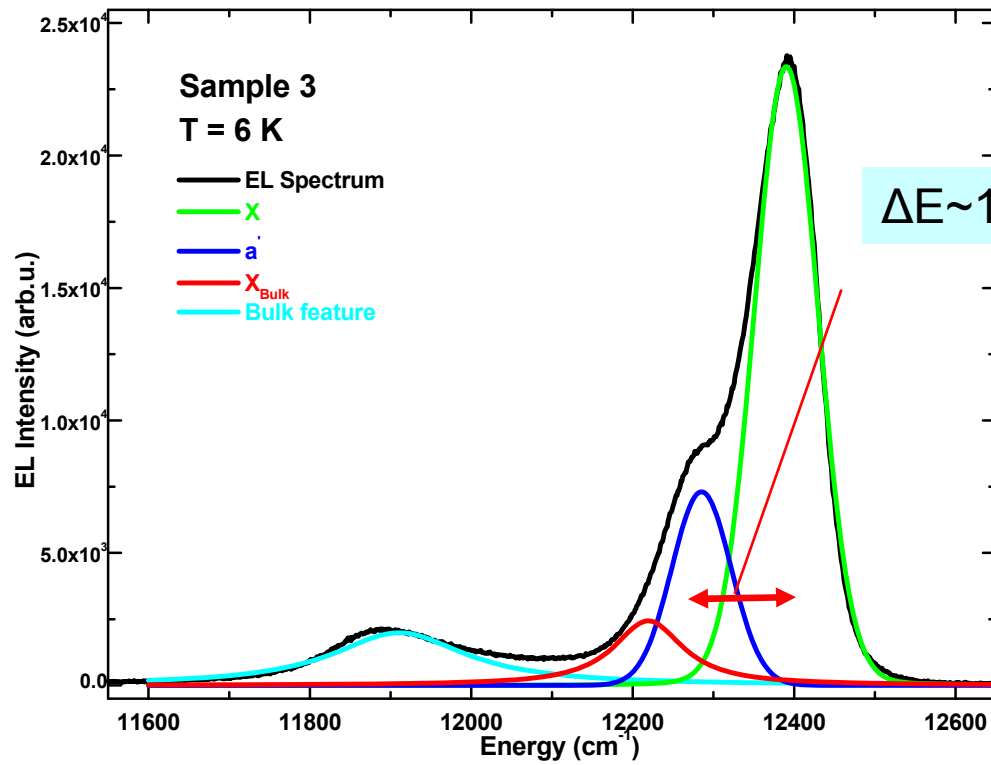


$\Delta E \sim 84 \text{ cm}^{-1} = \text{TA phonon at X}$



Spin-LED

Electroluminescence (1,1,0)



Questions?